

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:	PATENT APPLICATION
Inventors: Wei Gao, and Yoshi Ono	
Serial No: Not Yet Assigned	Attorney Docket No. SLA0782
Filed: Herewith	
Title: METHOD OF DEPOSITING A CONDUCTIVE NIOBIUM MONOXIDE FILM FOR MOSFET GATES	

Hon. Commissioner for Patents  
Washington, D.C. 20231

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to  
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by  
the Examiner and made of record in the above-identified application.

September 30, 2003

(Date)

Respectfully submitted,



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FORM PTO-1449  INFORMATION DISCLOSURE CITATION IN AN APPLICATION	DOCKET NUMBER SLA0782	APPLICATION NUMBER
	APPLICANT Wei Gao, and Yoshi Ono	
	FILING DATE: September 30, 2003	GROUP ART UNIT

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

## OTHER DOCUMENTS

	Article entitled: Nb Oxide Thin Film Resistors; by Wilson <i>et al.</i> , published in IEEE Transactions on Applied Superconductivity, Vol.9 No. 2, June 1999.
	Article entitled: Properties of Ru-Ta Alloys as Gate Electrodes For NMOS and PMOS Silicon Devices, by Zhong <i>et al.</i> , IEEE, 2001
	Article entitled: Tunable Work Function Molybdenum Gate Technology for FDSOI-CMOS, by Ranade <i>et al.</i> , IEEE 2002
	Article entitled: A Phase Map for Sputter Deposited Niobium Oxides, by Lee and Aita, published in the Journal of Applied Physics, Vol. 70, No. 4, 15 August 1991
EXAMINER	DATE CONSIDERED